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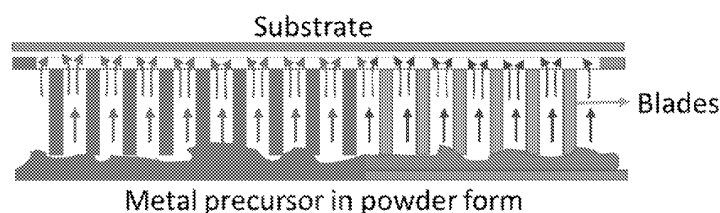
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FIG. 2



(57) Abstract: Herein disclosed is a device structurally configured to render a continuous layer of semiconducting material to form on a substrate, the device includes one or more blade structures, wherein each of the one or more blade structures have (i) one end which a precursor source is to be placed proximal to and (ii) the other end spaced apart from the substrate, and a supporting structure arranged peripheral to the one or more blade structures for supporting the substrate to be placed thereon or therewith, wherein the one or more blade structures are arranged to define one or more spaces which direct vapor produced from the precursor source toward the other end of each of the one or more blade structures, and wherein (i) the supporting structure, (ii) the substrate to be placed thereon, and (iii) the one or more blade structures define an area which confines the vapor to the area, thereby having the continuous layer of semiconducting material formed on a surface of the substrate which is adjacent to the area.



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